

US 20100193799A1

### (19) United States

## (12) Patent Application Publication

Nakano et al.

(10) **Pub. No.: US 2010/0193799 A1**(43) **Pub. Date: Aug. 5, 2010** 

# (54) SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE

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(21) Appl. No.: 12/654,620
(22) Filed: Dec. 24, 2009

#### (30) Foreign Application Priority Data

 Dec. 24, 2009 (JP) ...... 2009-293362

#### **Publication Classification**

(51) Int. Cl. H01L 29/78 (2006.01) H01L 21/336 (2006.01) H01L 29/24 (2006.01)

(52) **U.S. Cl.** .............. **257/77**; 257/330; 438/589; 438/270; 257/E29.104; 257/E29.262; 257/E21.41

#### (57) ABSTRACT

The semiconductor device according to the present invention includes: a semiconductor layer of a first conductivity type made of SiC having an Si surface; a gate trench dug down from the surface of the semiconductor layer; a gate insulating film formed on a bottom surface and a side surface of the gate trench so that the ratio of the thickness of a portion located on the bottom surface to the thickness of a portion located on the side surface is 0.3 to 1.0; and a gate electrode embedded in the gate trench through the gate insulating film.

